What is claimed is:

1. A bipolar transistor structure comprising:

a collector region having a first conductivity type formed in a semiconductor substrate;

a base region having a second conductivity type opposite the first conductivity type formed on the collector region, the base region including a lower highly doped layer formed on the collector region and a relatively low doped upper layer formed on the lower layer; and

an emitter region having the first conductivity type formed on the upper layer of the base region.

2. A bipolar transistor structure as in claim 1, and wherein the base region comprises a silicon/germanium (SiGe) layer that includes a lower highly doped SiGe layer formed on the collector and a low doped upper SiGe layed formed on the lower layer.

3. A bipolar transistor structure as in claim 2, and wherein the dopant in the both the lower SiGe and the upper SiGe layer comprises boron.

4. A bipolar transistor structure as in claim 1, and wherein the base region comprises a silicon/germanium layer a lower doped SiGe layer formed on the collector and on undoped upper SiGe layer formed in the lower layer.

5. A method for forming a bipolar transistor structure, the method comprising:

forming a collector region having a first conductivity type opposite the first conductivity type, the base region including a

lower highly doped layer formed on the collection region and a relatively low doped upper layer formed on the lower; and

forming on emitter region having the first conductivity type on the upper layer of the base region.

6. A method as in claim 5, and wherein the step of forming the base region comprises:

forming a lower doped SiGe layer on the collector utility a first dopant concentration; and

forming an upper doped SiGe layer on the lower SiGe layer utilizing a second dopant concentration that is less than the first dopant concentration.

7. A method as in claim 6, and wherein the second dopant concentration is zero.